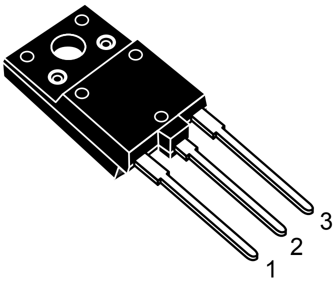
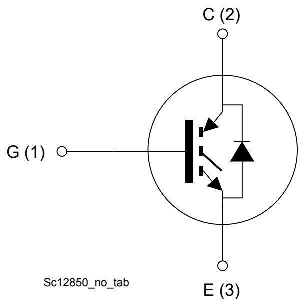
STGFW30V60DF

Datasheet

Trench gate field-stop IGBT, V series 600 V, 30 A very high speed



TO-3PF



Features

- Maximum junction temperature: T_J = 175 °C
- Tail-less switching off
- $V_{CE(sat)}$ = 1.85 V (typ.) @ I_C = 30 A
- Tight parameter distribution
- Safe paralleling
- Low thermal resistance
- Very fast soft recovery antiparallel diode

Applications

- Photovoltaic inverters
- Uninterruptible power supply
- Welding
- Power factor correction
- Very high frequency converters

Description

This device is an IGBT developed using an advanced proprietary trench gate field-stop structure. The device is part of the V series IGBTs, which represent an optimum compromise between conduction and switching losses to maximize the efficiency of very high frequency converters. Furthermore, the positive $V_{CE(sat)}$ temperature coefficient and very tight parameter distribution result in safer paralleling operation.

Product status link
STGFW30V60DF

Product summary	
Order code	STGFW30V60DF
Marking	G30V60DF
Package	TO-3PF
Packing	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage (V_{GE} = 0 V)	600	V
I_C	Continuous collector current at T_C = 25 °C	60	A
	Continuous collector current at T_C = 100 °C	30	
I_{CP} (1)	Pulsed collector current	120	A
V_{GE}	Gate-emitter voltage	±20	V
I_F	Continuous forward current at T_C = 25 °C	60	A
	Continuous forward current at T_C = 100 °C	30	
I_{FP} (1)	Pulsed forward current	120	
P_{TOT}	Total power dissipation at T_C = 25 °C	58	W
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s, T_C = 25 °C)	3.5	kV
T_{STG}	Storage temperature range	- 55 to 150	°C
T_J	Operating junction temperature range	- 55 to 175	

1. *Pulse width limited by maximum junction temperature.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case IGBT	2.6	°C/W
	Thermal resistance junction-case diode	3.4	
R_{thJA}	Thermal resistance junction-ambient	50	

2 Electrical characteristics

T_J = 25 °C unless otherwise specified

Table 3. Static characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	V_{GE} = 0 V, I_C = 2 mA	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	V_{GE} = 15 V, I_C = 30 A		1.85	2.3	V
		V_{GE} = 15 V, I_C = 30 A, T_J = 125 °C		2.15		
		V_{GE} = 15 V, I_C = 30 A, T_J = 175 °C		2.35		
V_F	Forward on-voltage	I_F = 30 A		2	2.6	V
		I_F = 30 A, T_J = 125 °C		1.7		
		I_F = 30 A, T_J = 175 °C		1.6		
$V_{GE(th)}$	Gate threshold voltage	V_{CE} = V_{GE}, I_C = 1 mA	5	6	7	V
I_{CES}	Collector cut-off current	V_{GE} = 0 V, V_{CE} = 600 V			25	µA
I_{GES}	Gate-emitter leakage current	V_{CE} = 0 V, V_{GE} = ±20 V			250	nA

Table 4. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	V_{CE} = 25 V, f = 1 MHz, V_{GE} = 0 V	-	3750	-	pF
C_{oes}	Output capacitance		-	120	-	pF
C_{res}	Reverse transfer capacitance		-	77	-	pF
Q_g	Total gate charge	V_{CC} = 480 V, I_C = 30 A, V_{GE} = 15 V (see Figure 27. Gate charge test circuit)	-	163	-	nC
Q_{ge}	Gate-emitter charge		-	28	-	nC
Q_{gc}	Gate-collector charge		-	72	-	nC

Table 5. **IGBT switching characteristics (inductive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{CE} = 400 V, I_C = 30 A, R_G = 10 Ω, V_{GE} = 15 V (see Figure 26. Test circuit for inductive load switching)	-	45	-	ns
t_r	Current rise time		-	16	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	1500	-	A/μs
$t_{d(off)}$	Turn-off delay time		-	189	-	ns
t_f	Current fall time		-	19	-	ns
E_{on} [(1)]	Turn-on switching energy		-	383	-	μJ
E_{off} [(2)]	Turn-off switching energy		-	233	-	μJ
E_{ts}	Total switching energy		-	616	-	μJ
$t_{d(on)}$	Turn-on delay time	V_{CE} = 400 V, I_C = 30 A, R_G = 10 Ω, V_{GE} = 15 V, T_J = 175 °C (see Figure 26. Test circuit for inductive load switching)	-	42	-	ns
t_r	Current rise time		-	17	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	1337	-	A/μs
$t_{d(off)}$	Turn-off-delay time		-	193	-	ns
t_f	Current fall time		-	32	-	ns
E_{on} [(1)]	Turn-on switching energy		-	794	-	μJ
E_{off} [(2)]	Turn-off switching energy		-	378	-	μJ
E_{ts}	Total switching energy		-	1172	-	μJ

1. *Energy losses include reverse recovery of the diode.*
2. *Turn-off losses include also the tail of the collector current.*

Table 6. **Diode switching characteristics (inductive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	I_F = 30 A, V_R = 400 V, V_{GE} = 15 V, di/dt = 1000 A/μs (see Figure 26. Test circuit for inductive load switching)	-	53	-	ns
Q_{rr}	Reverse recovery charge		-	384	-	nC
I_{rrm}	Reverse recovery current		-	14.5	-	A
dI_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	788	-	A/μs
E_{rr}	Reverse recovery energy		-	104	-	μJ
t_{rr}	Reverse recovery time	I_F = 30 A, V_R = 400 V, V_{GE} = 15 V, di/dt = 1000 A/μs, T_J = 175 °C (see Figure 26. Test circuit for inductive load switching)	-	104	-	ns
Q_{rr}	Reverse recovery charge		-	1352	-	nC
I_{rrm}	Reverse recovery current		-	26	-	A
dI_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	310	-	A/μs
E_{rr}	Reverse recovery energy		-	407	-	μJ

2.1 Electrical characteristics (curves)

Figure 1. Power dissipation vs case temperature

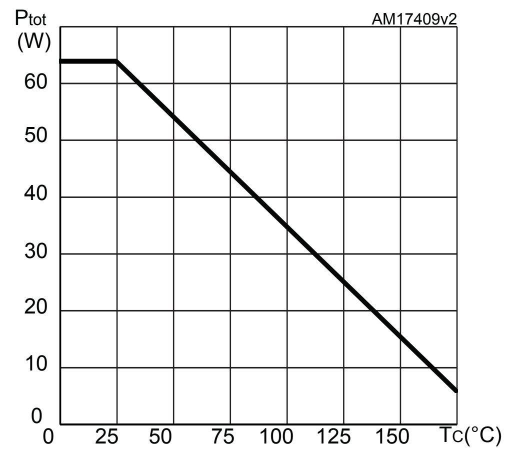


Figure 2. Collector current vs case temperature

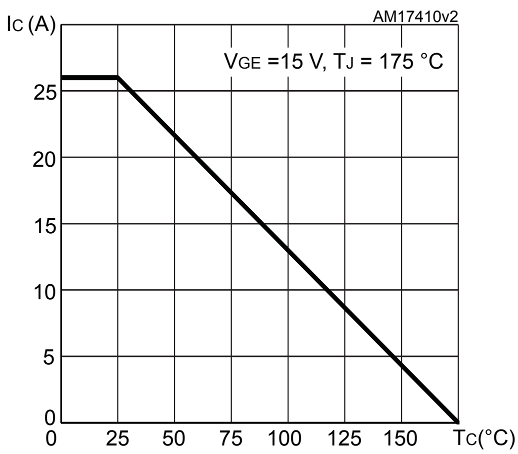


Figure 3. Output characteristics (T_J = 25 °C)

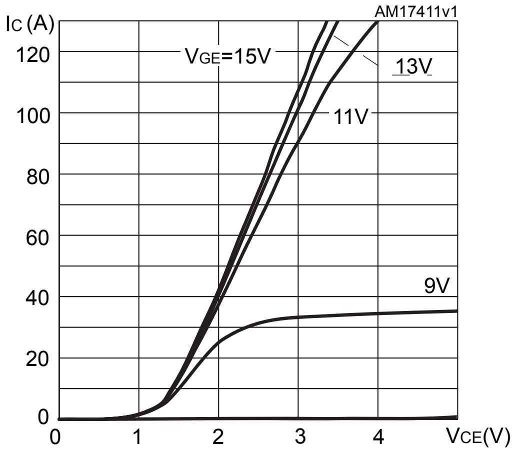


Figure 4. Output characteristics (T_J = 175 °C)

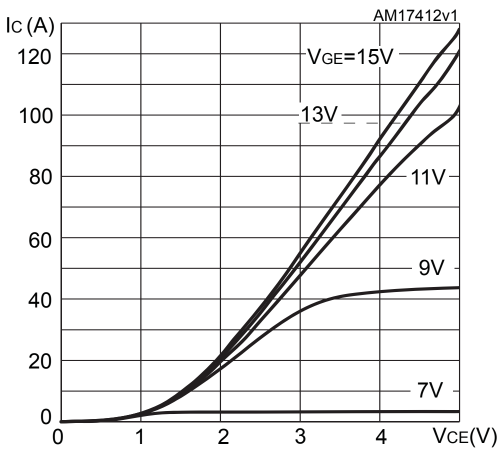


Figure 5. V_{CE}(sat) vs junction temperature

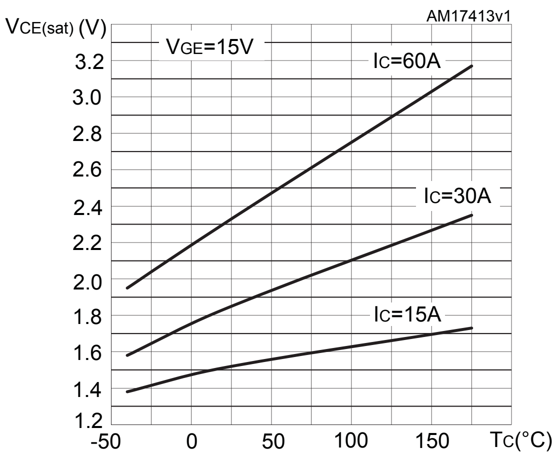


Figure 6. V_{CE}(sat) vs collector current

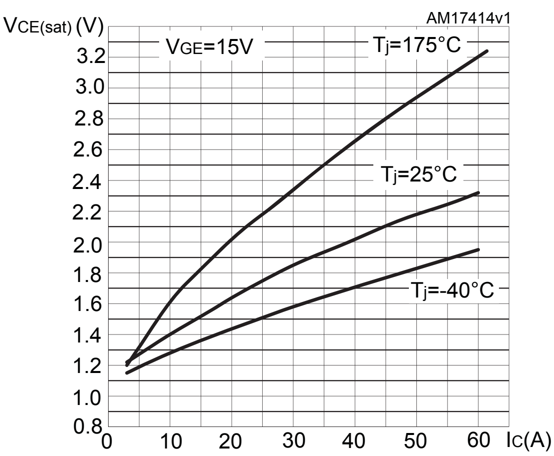


Figure 7. **Transfer characteristics**

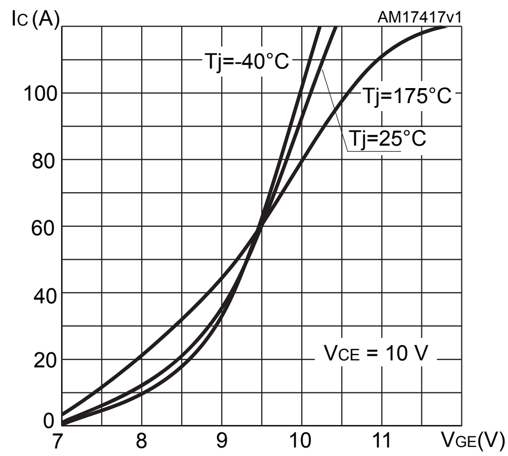


Figure 8. **Diode V_F vs forward current**

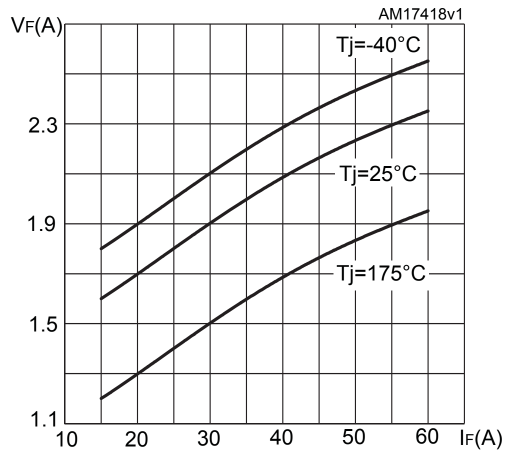


Figure 9. **Normalized $V_{GE(th)}$ vs junction temperature**

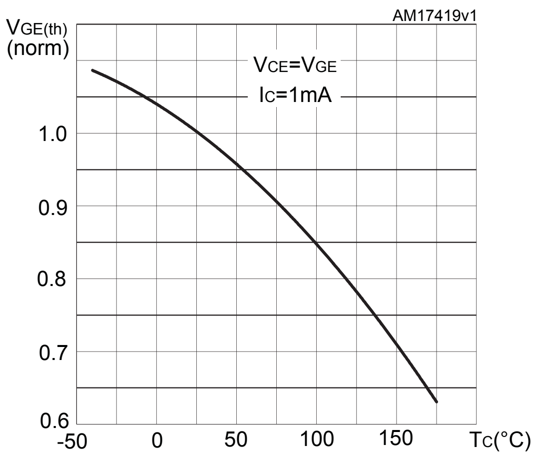


Figure 10. **Normalized $V_{(BR)CES}$ vs junction temperature**

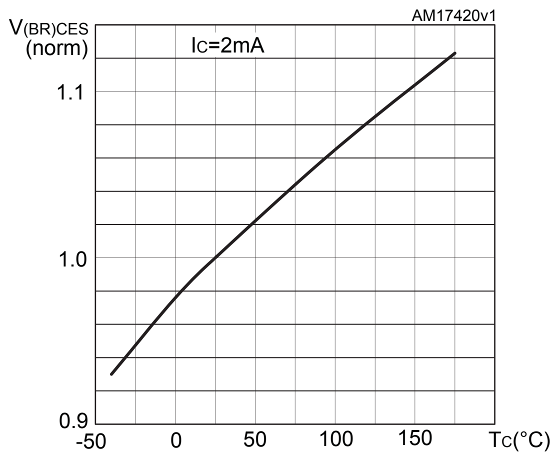


Figure 11. **Capacitance variations**

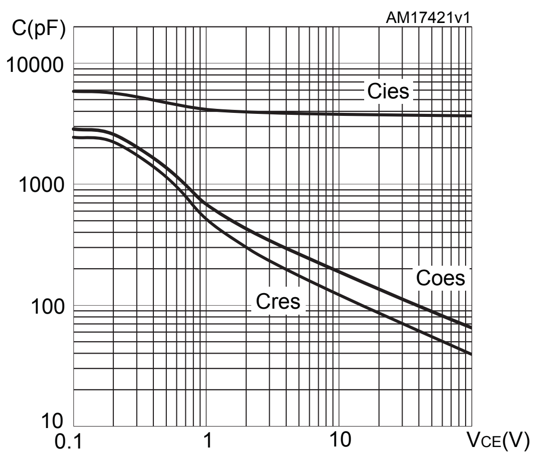


Figure 12. **Gate charge vs gate-emitter voltage**

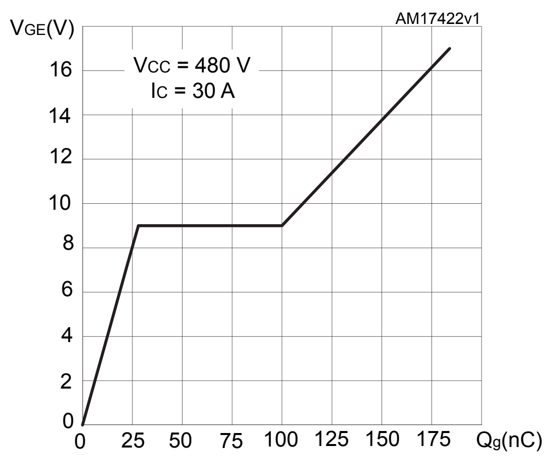


Figure 13. Switching energy vs collector current

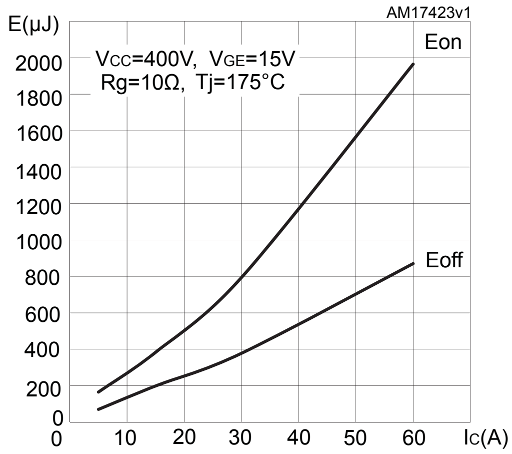


Figure 14. Switching energy vs gate resistance

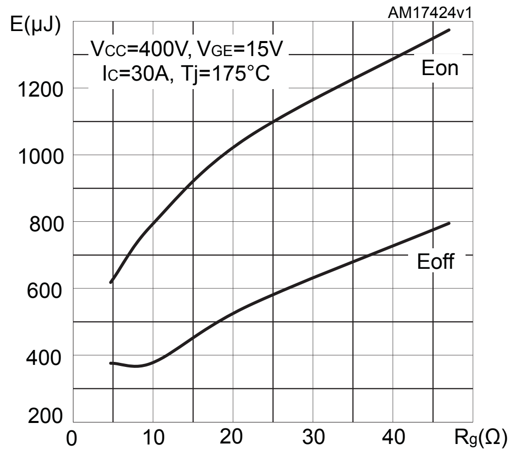


Figure 15. Switching energy vs junction temperature

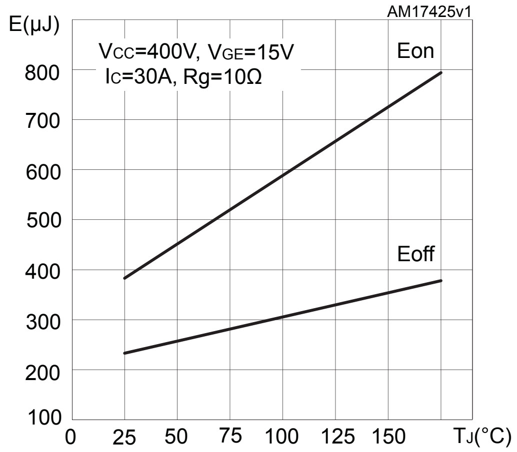


Figure 16. Switching energy vs collector-emitter voltage

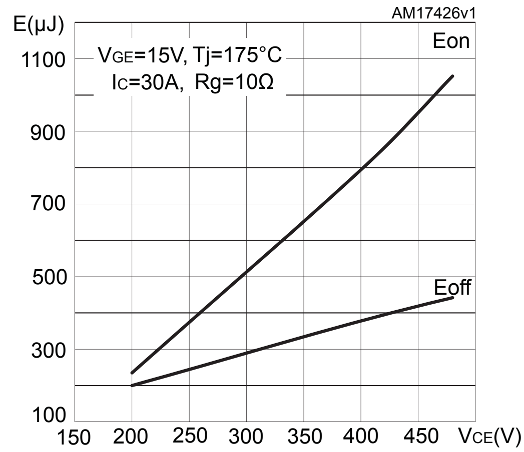


Figure 17. Switching times vs collector current

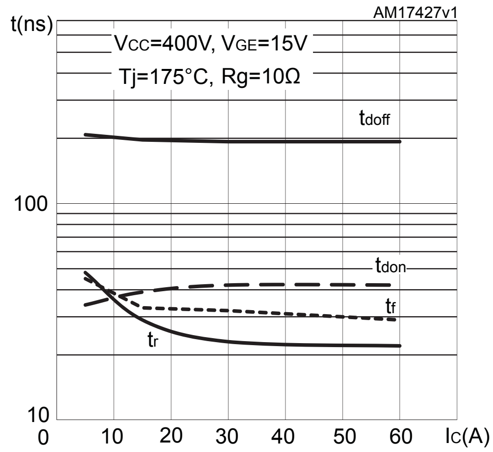


Figure 18. Switching times vs gate resistance

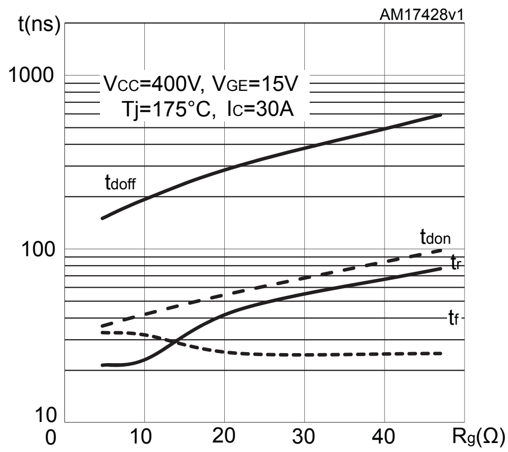


Figure 19. Reverse recovery current vs diode current slope

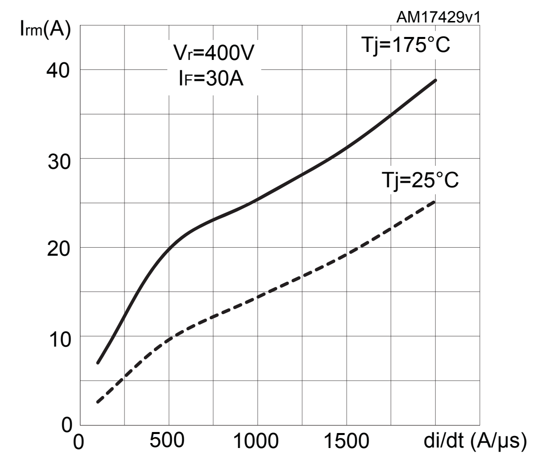


Figure 20. Reverse recovery time vs diode current slope

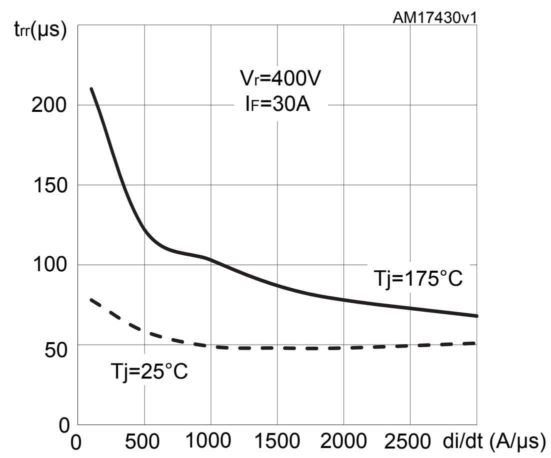


Figure 21. Reverse recovery charge vs diode current slope

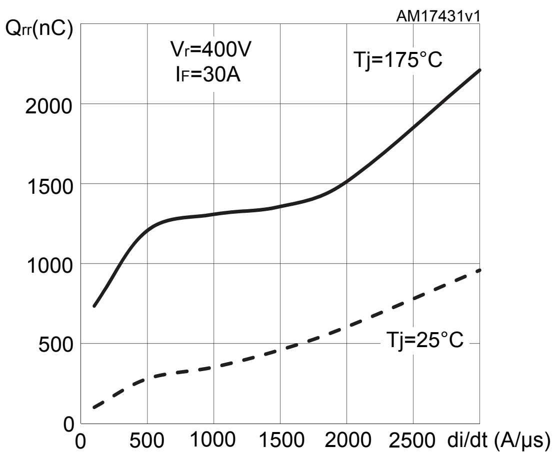


Figure 22. Reverse recovery energy vs diode current slope

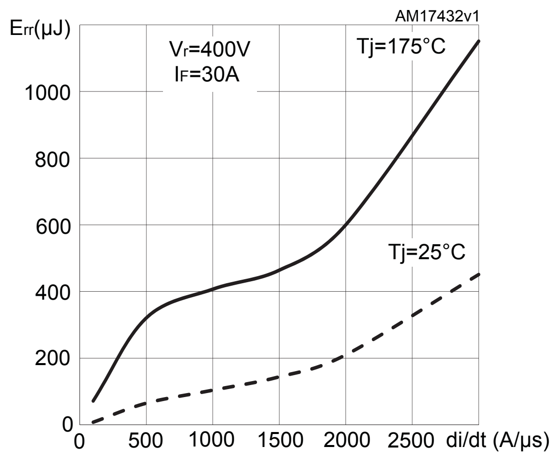
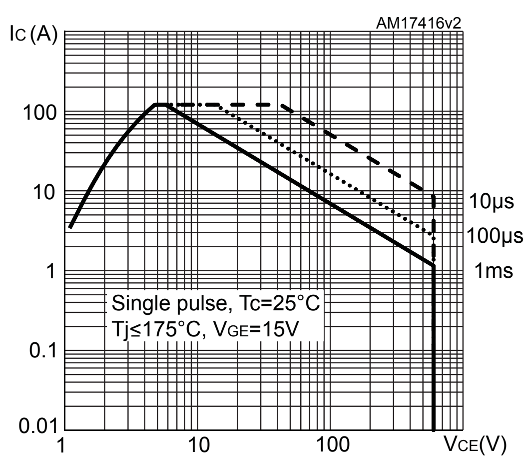


Figure 23. Safe operating area



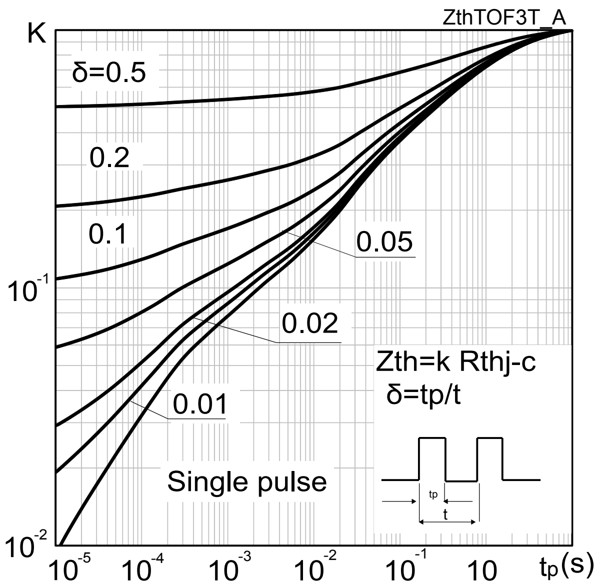


Figure 24. Thermal impedence for IGBT

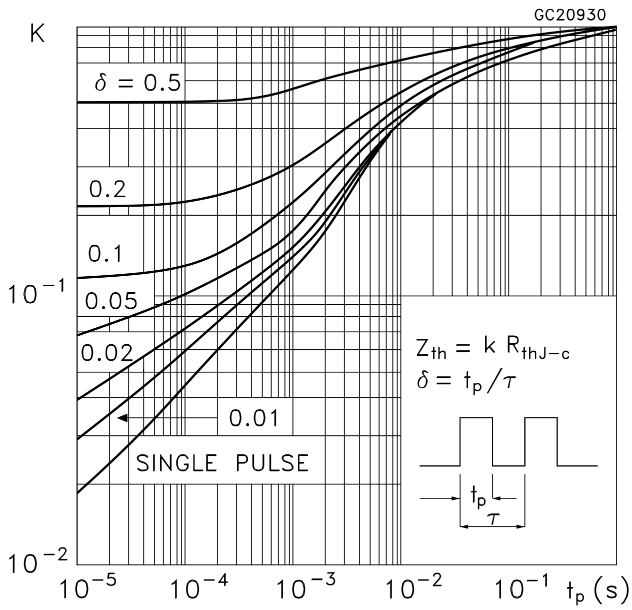


Figure 25. Thermal impedance for diode

3 Test circuits

Figure 26. Test circuit for inductive load switching

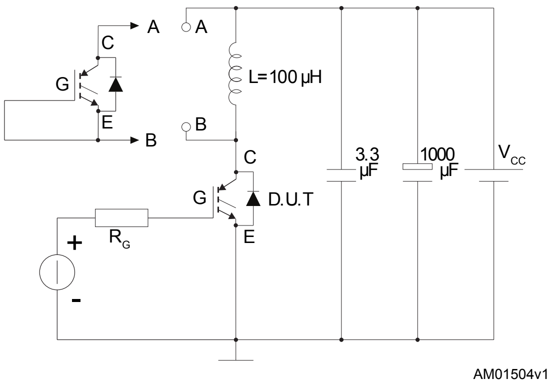


Figure 27. Gate charge test circuit

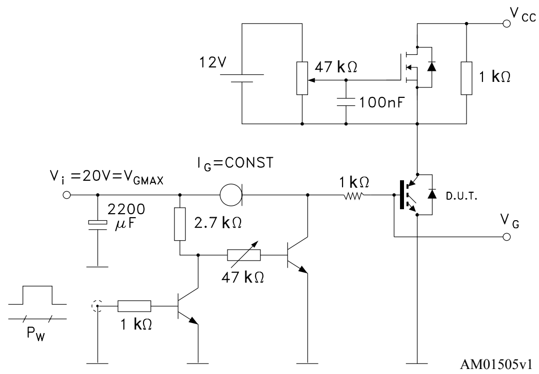


Figure 28. Switching waveform

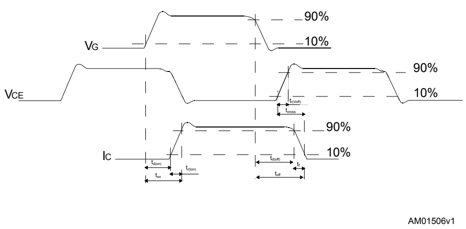
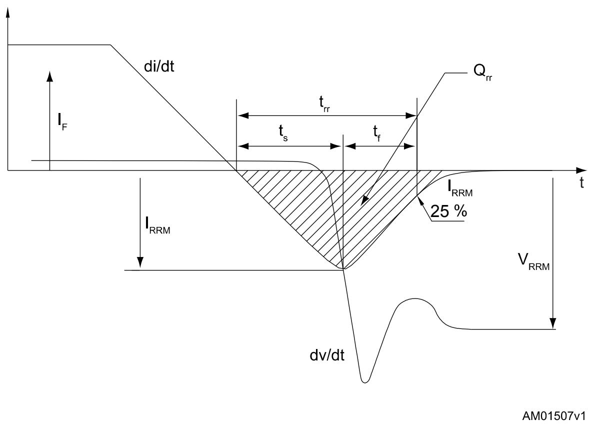


Figure 29. Diode reverse recovery waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-3PF package information

Figure 30. TO-3PF package outline

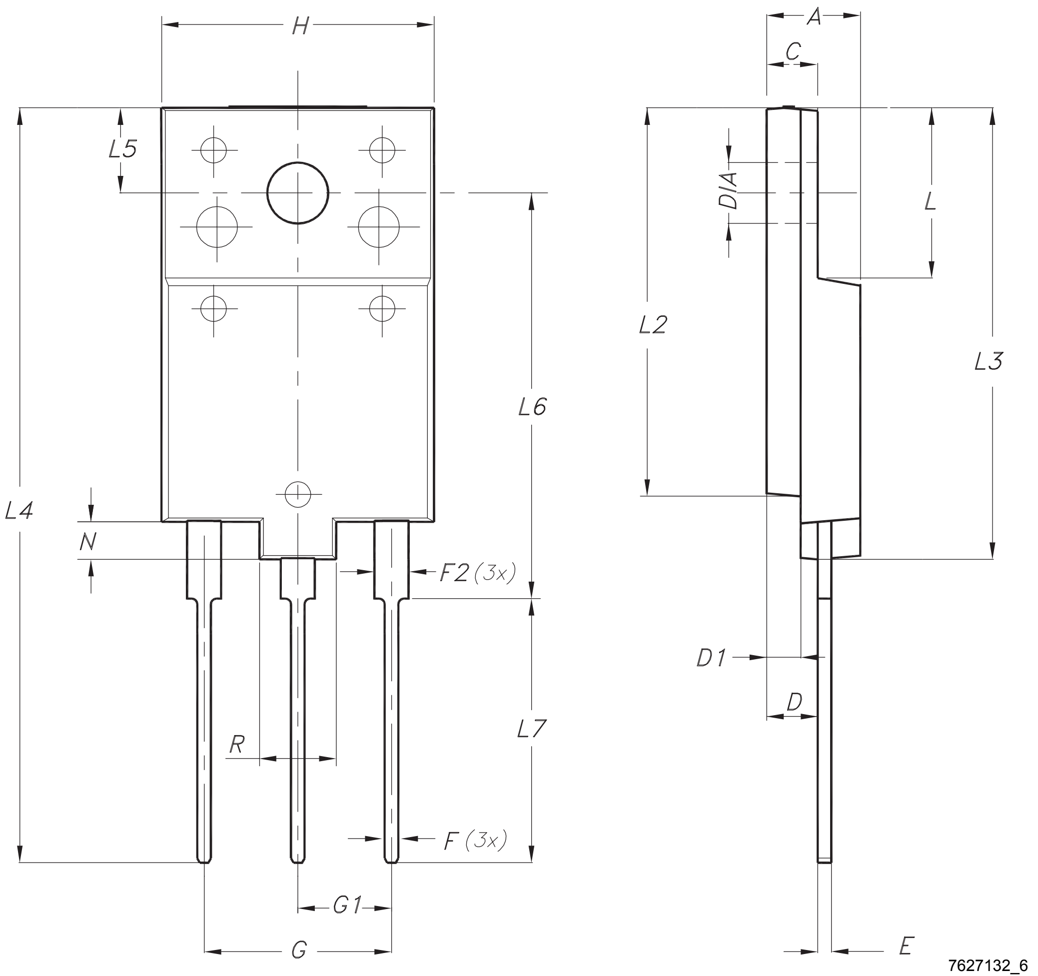


Table 7. TO-3PF mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	5.30		5.70
C	2.80		3.20
D	3.10		3.50
D1	1.80		2.20
E	0.80		1.10
F	0.65		0.95
F2	1.80		2.20
G	10.30		11.50
G1		5.45	
H	15.30		15.70
L	9.80	10.00	10.20
L2	22.80		23.20
L3	26.30		26.70
L4	43.20		44.40
L5	4.30		4.70
L6	24.30		24.70
L7	14.60		15.00
N	1.80		2.20
R	3.80		4.20
Dia	3.40		3.80

Revision history

Table 8. Document revision history

Date	Revision	Changes
31-Mar-2014	1	Initial release.
14-Apr-2020	2	Updated Section Product status / summary in cover page. Minor text changes.

Contents